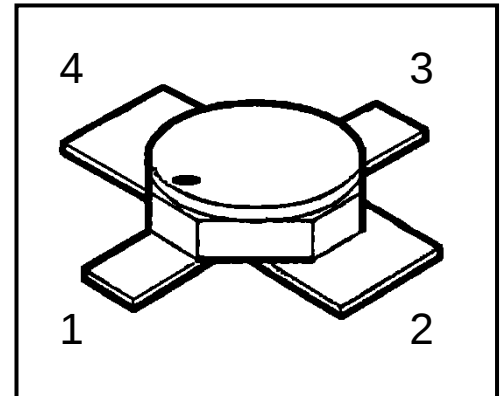


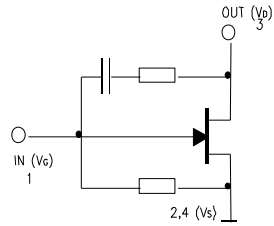
HiRel L- and S-Band GaAs General Purpose Amplifier

- **HiRel Discrete and Microwave Semiconductor**

- Single-stage monolithic microwave IC (MMIC-amplifier)
- Application range: 100 MHz to 3 GHz
- Gain: 9.5 dB typ. @ 1.8 GHz
- Low noise figure: 2.7 dB typ. @ 1.8 GHz
- Bandwidth: 3 GHz typ. @ -3 dB, VSWR < 2 : 1 *
Operating voltage range: 3 to 5.5 V
- Input and output matched to 50 Ω
- Individual current control with neg. gate bias
- Hermetically sealed ceramic package micro-x



ESD: **E**lectrostatic **d**ischarge sensitive device,
observe handling precautions!

Type	Marking	Ordering Code	Circuit Diagram (Pin Configuration)	Package
CGY41 (ql)	-	see below		Micro-X

(ql) Quality Level: P: Professional Quality,
H: High Rel Quality,
S: Space Quality,

Ordering Code: on request

Ordering Code: on request

Ordering Code: on request

(see order instructions for ordering example)

Maximum ratings	Symbol	Value	Unit
Drain-voltage	V_D	5.5	V
Gate-voltage	V_G	-4 ... 0.5	V
Drain-gate voltage	V_{DG}	9.5	V
RF Input power ¹⁾	P_{RFIN}	16	dBm
Channel temperature	T_{Ch}	175	°C
Storage temperature range	T_{stg}	-55...+175	°C
Total power dissipation ($T_s \leq 82^\circ\text{C}$) ²⁾	P_{tot}	440	mW
Thermal resistance			
Channel-soldering point ²⁾	R_{thChS}	160	K/W

Notes: Exceeding any of the max. ratings may cause permanent damage to the device. Appropriate handling is required to protect the electrostatic sensitive MMIC against degradation due to excess voltage or current spikes. Proper ground connection of leads 2 and 4 (with min. inductance) is required to achieve the guaranteed RF performance, stable operating conditions and adequate cooling.

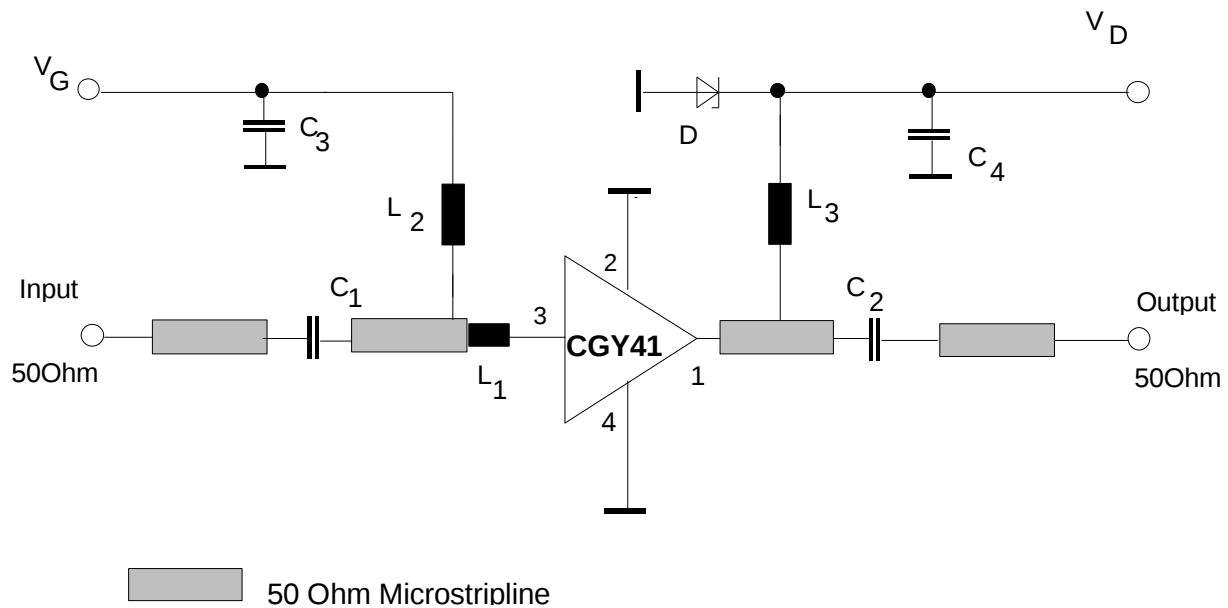
1) @ $V_D > 4.5$ V derating required.

2) T_s is measured on the source lead at the soldering point to the PCB.

Electrical Characteristics

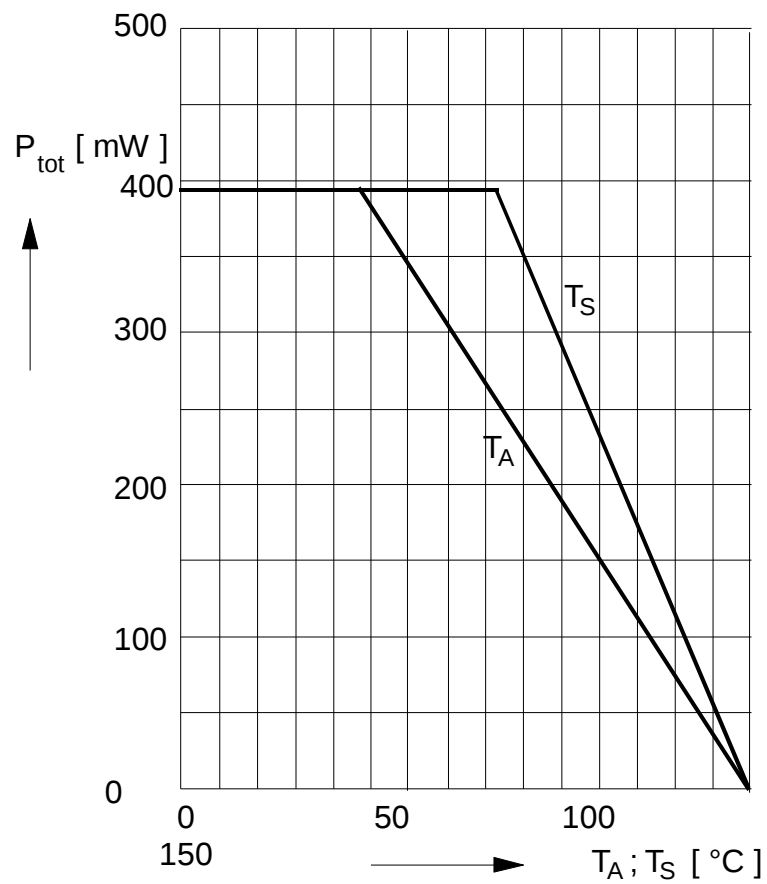
$T_A = 25\text{ }^{\circ}\text{C}$, $V_G = 0\text{ V}$, $V_D = 4.5\text{ V}$, $R_S = R_L = 50\text{ }\Omega$ unless otherwise specified
(for application circuit see next page)

Characteristics	Symbol	min	typ	max	Unit
Drain current	I_{DSS}	40	60	80	mA
Power gain f = 200 MHz f = 1800 MHz	G	9.5 8.5	10.5 9.5	13 11	dB
Gain flatness f = 200 to 1000 MHz f = 800 to 1800 MHz	GF	- -	0.4 1.1	- 2	dB
Noise figure f = 200 to 1000 MHz f = 800 to 1800 MHz	F	- -	2.5 2.7	- 4.0	dB
Input return loss f = 200 to 1000 MHz f = 800 to 1800 MHz	RL_{IN}	- -	13 12	- 9.5	dB
Output return loss f = 200 to 1000 MHz f = 800 to 1800 MHz	RL_{OUT}	- -	12 12	- 9.5	dB
Third order intercept point Two tone intermodulation test f ₁ = 806 MHz, f ₂ = 810 MHz P ₀ = 10 dBm (both carriers)	$IP3$	31	32	-	dBm
1dB gain compression f = 200 to 1800 MHz	$P_{1\text{ dB}}$	-	18	-	dBm

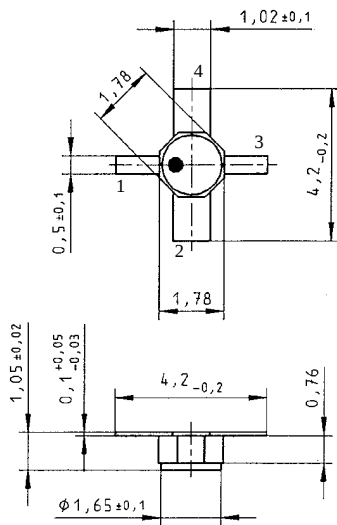
Application Circuit ($f = 800$ to 1800 MHz)

Legend of components

C_1, C_2	Chip capacitors 100 pF
C_3, C_4	Chip capacitors 1 nF
L_1	For optimized input matching - discrete inductor: approx. 3nH, or - printed microstripline inductor: Z approx. 100 $\square\square$ l_e approx. 5 mm
L_2, L_3	- discrete inductor: approx. 40 nH, as e.g. 5 turns 0.25 mm copper wire on nylon rod with M3-thread, or - printed microstripline inductor
D	Z diode 5.6 V (type BZW 22 C5 V 6)

Total Power Dissipation $P_{\text{tot}} = f(T_S; T_A)$



Micro-X Package



Edition 2011-02

Published by

Infineon Technologies AG

85579 Neubiberg, Germany

© Infineon Technologies AG 2011

All Rights Reserved.

Attention please!

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of a third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.